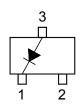
#### SILICON EPITAXIAL PLANAR SWITCHING DIODE

#### **Applications**

• for switching circuits





## Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V <sub>RM</sub>	80	V
Reverse Voltage	$V_R$	80	V
Forward Current	I <sub>F</sub>	100	mA
Peak Forward Current	I <sub>FM</sub>	225	mA
Non-repetitive Peak Forward Surge Current (t = 1 s)	I <sub>FSM</sub>	500	mA
Junction Temperature	TJ	150	°C
Storage Temperature Range	Ts	- 55 to + 150	°C

## Characteristics at $T_a = 25$ °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I <sub>F</sub> = 100 mA	$V_{F}$	-	1.2	V
Reverse Current at V <sub>R</sub> = 75 V	I <sub>R</sub>	-	0.1	μΑ
Reverse Voltage at I <sub>R</sub> = 100 μA	$V_{R}$	80	-	V
Terminal Capacitance at $V_R = 0$ , $f = 1$ MHz	C <sub>t</sub>	-	15	pF
Reverse Recovery Time at $I_F$ = 10 mA, $V_R$ = 6 V, $I_{rr}$ = 0.1 • $I_R$ , $R_L$ = 100 $\Omega$	t <sub>rr</sub>	-	10	ns

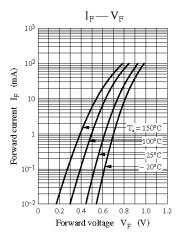


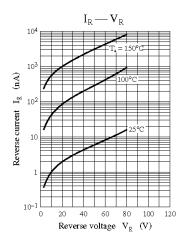


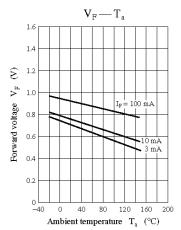


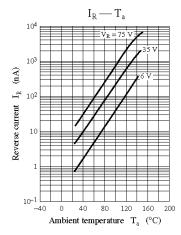
SEMTECH ELECTRONICS LTD.

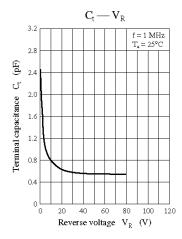
(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

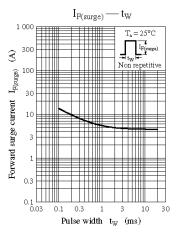














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Dated: 17/10/2007